

**Silicon PNP Power Transistor**

**2SB861**

**DESCRIPTION**

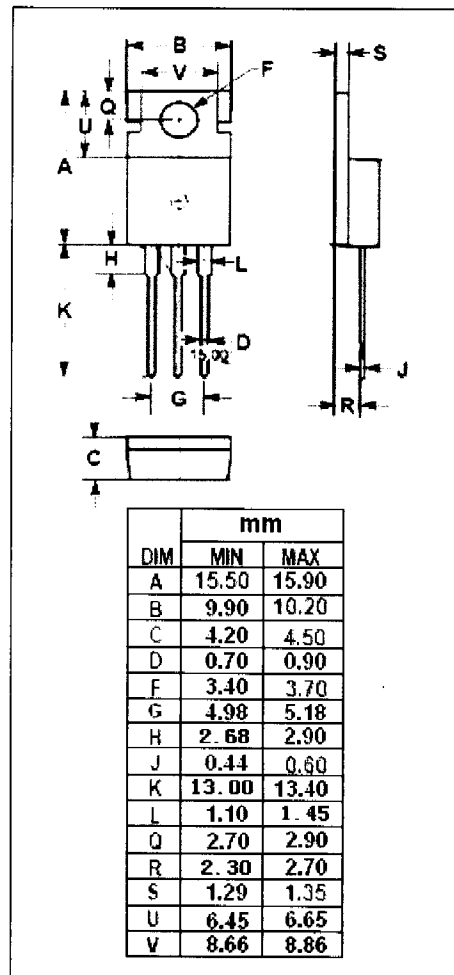
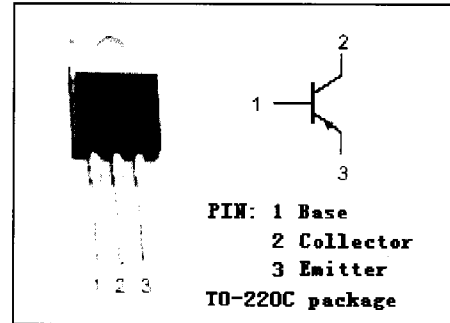
- High Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -150V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SD1138

**APPLICATIONS**

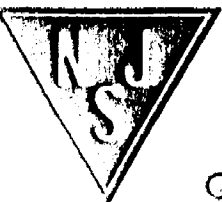
- Developed for low frequency power amplifier color TV vertical deflection output applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-200	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-2	A
$I_{CM}$	Collector Current-Peak	-5	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.8	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-45~150	$^\circ\text{C}$



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### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}$ ; $R_{BE} = \infty$	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -5\text{mA}$ ; $I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$ ; $I_B = -50\text{mA}$			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -50\text{mA}$ ; $V_{CE} = -4\text{V}$			-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -120\text{V}$ ; $I_E = 0$			-1	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -50\text{mA}$ ; $V_{CE} = -4\text{V}$	60		200	
$h_{FE-2}$	DC Current Gain	$I_C = -500\text{mA}$ ; $V_{CE} = -10\text{V}$	60			
$C_{OB}$	Output Capacitance	$I_E = 0$ ; $V_{CB} = -100\text{V}$ ; $f_{test} = 1.0\text{MHz}$		30		pF

#### ◆ $h_{FE-1}$ Classifications

B	C
60-120	100-200